

IN THE CLAIMS

Please cancel Claims 10 to 20 without prejudice to or disclaimer of the subject matter presented therein and without prejudice to Applicants' right to present these claims in a later-filed division. The claims, as pending in the subject application, read as follows:

1. (Previously Presented) A liquid phase growth method comprising the steps of: immersing a substrate in a crucible that stores a solvent having a growth material dissolved therein; and

flowing a medium through a medium flow path provided in the solvent, without blowing the medium up through the solvent, to cool the solvent from an interior thereof.

2. (Original) The liquid phase growth method according to Claim 1, wherein the solvent is cooled from a central part thereof.

3. (Previously Presented) The liquid phase growth method according to Claim 1, wherein the medium flow path comprises a tube through which the medium flows immersed in the crucible.

4. (Previously Presented) The liquid phase growth method according to Claim 1, wherein the medium flow path comprises a tube through which the medium flows formed in a jig for holding the substrate.

5. (Previously Presented) The liquid phase growth method according to Claim 1, wherein the medium flow path comprises a hole through which the medium flows formed in the crucible.

6. (Original) The liquid phase growth method according to Claim 3, wherein the medium is a gas.

7. (Original) The liquid phase growth method according to Claim 1, wherein a liquid phase growth bath for formation of a p<sup>-</sup> type Si layer is used as the crucible and, subsequent thereto, a liquid phase growth bath for formation of an n<sup>+</sup> type Si layer is used as the crucible.

8. (Original) The liquid phase growth method according to Claim 1, wherein the growth material is Si, Ge, or GaAs.

9. (Original) The liquid phase growth method according to Claim 1, wherein the solvent is a melt of In or Sn.

10 to 20. (Cancelled)